

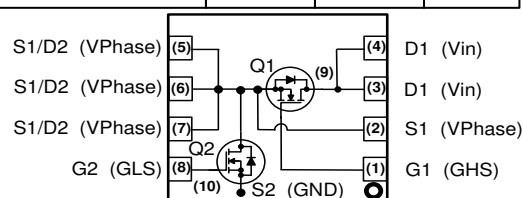
Power Block

Features

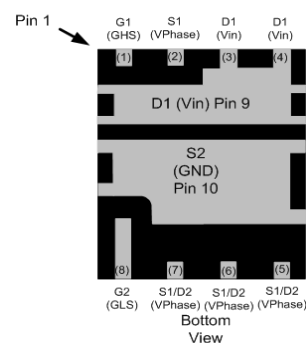
- Dual asymmetric N-channel OptiMOS™5 MOSFET
- Logic level (4.5V rated)
- Pb-free lead plating; RoHS compliant
- Optimized for high performance Buck converter
- Qualified according to JEDEC¹⁾ for target applications
- Halogen-free according to IEC61249-2-21
- Monolithic integrated Schottky like diode

Product Summary

		Q1	Q2	
V_{DS}		25	25	V
$R_{DS(on),max}$	$V_{GS}=10\text{ V}$	3	0.85	$m\Omega$
	$V_{GS}=4.5\text{ V}$	4	1.2	
I_D		50	50	A



Top view



Type	Package	Marking
BSG0810NDI	PG-TISON8-4	0810NDI

Maximum ratings, at $T_j=25^\circ\text{C}$, unless otherwise specified ²⁾

Parameter	Symbol	Conditions	Value		Unit
			Q1	Q2	
Continuous drain current	I_D	$T_C=70^\circ\text{C}$, $V_{GS}=10\text{ V}$	50	50	A
		$T_C=70^\circ\text{C}$, $V_{GS}=4.5\text{ V}$	50	50	
		$T_A=25^\circ\text{C}$, $V_{GS}=4.5\text{ V}^{(3)}$	31	50	
		$T_A=25^\circ\text{C}$, $V_{GS}=4.5\text{ V}^{(4)}$	19	39	
Pulsed drain current	$I_{D,pulse}$	$T_C=70^\circ\text{C}$	160	160	
Avalanche energy, single pulse	E_{AS}	Q1: $I_D=10\text{ A}$, Q2: $I_D=20\text{ A}$, $R_{GS}=25\ \Omega$	30	90	mJ
Gate source voltage	V_{GS}	$T_j=25^\circ\text{C}$	± 16		V
Power dissipation	P_{tot}	$T_A=25^\circ\text{C}^{(3)}$	6.25	6.25	W
		$T_A=25^\circ\text{C}^{(4)}$	2.5	2.5	
Operating and storage temperature	T_j , T_{stg}		-55 ... 150		$^\circ\text{C}$
IEC climatic category; DIN IEC 68-1			55/150/56		

¹⁾ J-STD20 and JESD22

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Thermal characteristics

Thermal resistance, junction - case	Q1	R_{thJC}		-	-	4.3	K/W
	Q2			-	-	1.8	
Thermal resistance, junction - ambient ²⁾	Q1	R_{thJA}	Application specific board ³⁾	-	-	20	
	Q2			-	-		
	Q1		6 cm ² cooling area ⁴⁾	-	-	50	
	Q2			-	-		

Electrical characteristics, at $T_j=25\text{ °C}$, unless otherwise specified

Static characteristics

Drain-source breakdown voltage	Q1	$V_{(BR)DSS}$	$V_{GS}=0\text{ V}, I_D=1\text{ mA}$	25 ⁶⁾	-	-	V
	Q2						
Breakdown voltage temperature coefficient	Q1	$dV_{(BR)DSS}/dT_j$	$I_D=10\text{ mA}$, referenced to 25 °C	-	15	-	mV/K
	Q2						
Gate threshold voltage	Q1	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\text{ }\mu\text{A}$	1.2	1.6	2	V
	Q2						
Zero gate voltage drain current	Q1	I_{DSS}	$V_{DS}=25\text{ V}, V_{GS}=0\text{ V}, T_j=25\text{ °C}$	-	-	1	μA
	Q2			-	-	500	
	Q1		$V_{DS}=20\text{ V}, V_{GS}=0\text{ V}, T_j=125\text{ °C}$	-	-	100	mA
	Q2			-	3	-	
Gate-source leakage current	Q1	I_{GSS}	$V_{GS}=16\text{ V}, V_{DS}=0\text{ V}$	-	-	100	nA
	Q2						
Drain-source on-state resistance	Q1	$R_{DS(on)}$	$V_{GS}=4.5\text{ V}, I_D=20\text{ A}$	-	3.2	4.0	m Ω
	Q2			-	1.0	1.1	
	Q1		$V_{GS}=10\text{ V}, I_D=20\text{ A}$	-	2.4	3.0	
	Q2			-	0.7	0.9	
Gate resistance	Q1	R_G		-	0.7	1.2	Ω
	Q2			-	0.8	1.3	
Transconductance	Q1	g_{fs}	$ V_{DS} >2 I_D R_{DS(on)max}, I_D=20\text{ A}$	47	94	-	S
	Q2			55	110	-	

²⁾ Remark: only one of both transistors active

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Dynamic characteristics

Input capacitance	Q1	C_{iss}	$V_{GS}=0\text{ V},$ $V_{DS}=12\text{ V}, f=1\text{ MHz}$	-	770	1040	pF
	Q2			-	2300	3100	
Output capacitance	Q1	C_{oss}		-	390	520	
	Q2			-	1400	1900	
Reverse transfer capacitance	Q1	C_{rss}		-	33	-	
	Q2			-	110	-	
Turn-on delay time	Q1	$t_{d(on)}$	$V_{IN}=12\text{ V},$ $V_{DRV}=5\text{ V},$ $F_{SW}=500\text{ KHz},$ $I_{OUT}=30\text{ A}^{5)}$	-	4.3	-	ns
	Q2			-	5.1	-	
Rise time	Q1	t_r		-	4.7	-	
	Q2			-	4.0	-	
Turn-off delay time	Q1	$t_{d(off)}$		-	4.3	-	
	Q2			-	8	-	
Fall time	Q1	t_f		-	1.4	-	
	Q2			-	2.4	-	

Gate Charge Characteristics

Gate to source charge	Q1	Q_{gs}	$V_{DD}=12\text{ V},$ $I_D=20\text{ A},$ $V_{GS}=0\text{ to }4.5\text{ V}$	-	2.2	-	nC
Gate to drain charge		Q_{gd}		-	1.6	-	
Gate charge total		Q_g		-	5.6	8.4	
Gate plateau voltage		$V_{plateau}$		-	2.9	-	V
Gate to source charge	Q2	Q_{gs}		-	5.9	-	nC
Gate to drain charge		Q_{gd}		-	4.2	-	
Gate charge total		Q_g		-	16	25	
Gate plateau voltage		$V_{plateau}$		-	2.6	-	V
Output charge	Q1	Q_{oss}	$V_{DD}=12\text{ V}, V_{GS}=0\text{ V}$	-	8	-	nC
	Q2			-	26	-	

³⁾ 8 Layers copper 70µm thickness. PCB in still air

⁴⁾ Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Reverse Diode

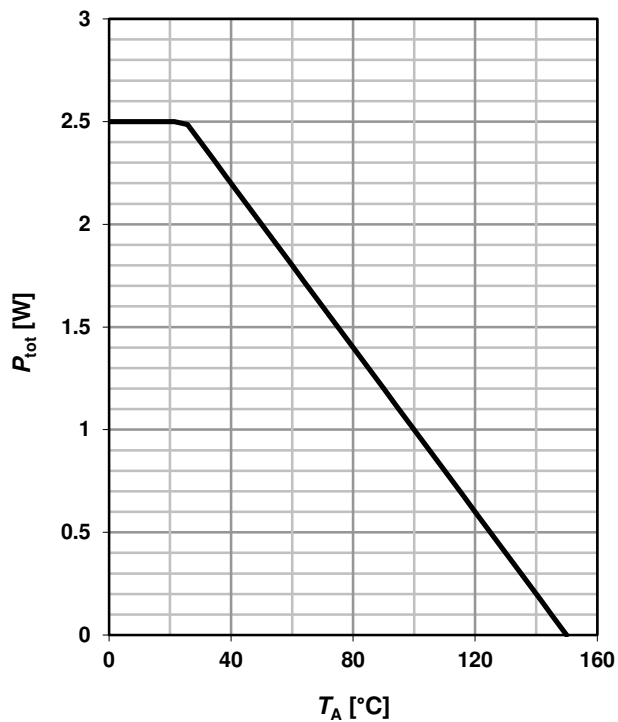
Diode continuous forward current	Q1	I_S	$T_C=25\text{ }^{\circ}\text{C}$	-	-	29	A
	Q2					50	
Diode pulse current	Q1	$I_{S,pulse}$		-	-	160	
	Q2			-	-	160	
Diode forward voltage	Q1	V_{SD}	$V_{GS}=0\text{ V}, I_F=20\text{ A},$ $T_j=25\text{ }^{\circ}\text{C}$	-	0.85	1	V
	Q2		$V_{GS}=0\text{ V}, I_F=11\text{ A},$ $T_j=25\text{ }^{\circ}\text{C}$	-	0.49	0.7	
Reverse recovery charge	Q1	Q_{rr}	$V_R=12\text{ V}, I_F=I_S,$ $di_F/dt=100\text{ A}/\mu\text{s}$	-	10	-	nC
	Q2						

⁵⁾ For more information see application note n° TBD

⁶⁾ The device can withstand a pulse of not more than 30V for a duration of up to 2ns at a frequency of 600KHz with maximum buck converter input voltage $V_{IN}=16\text{ V}$

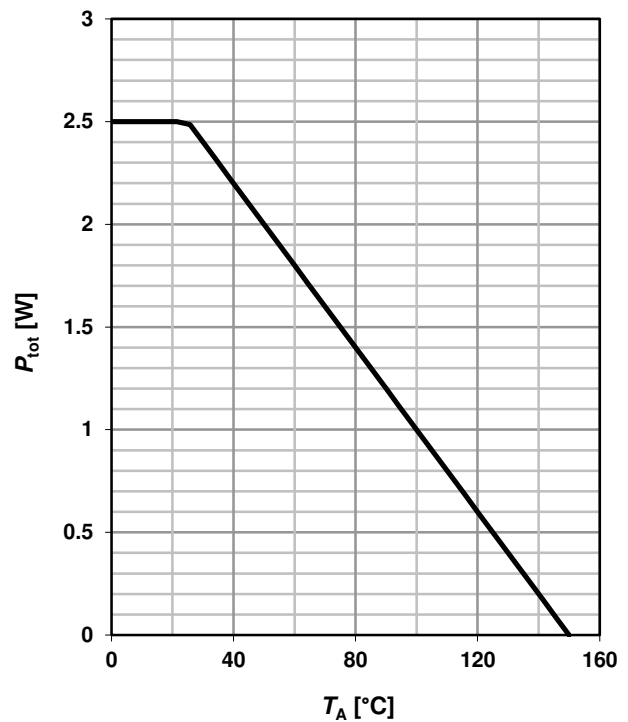
1 Power dissipation (Q1)

$$P_{\text{tot}} = f(T_A)^{(4)}$$



2 Power dissipation (Q2)

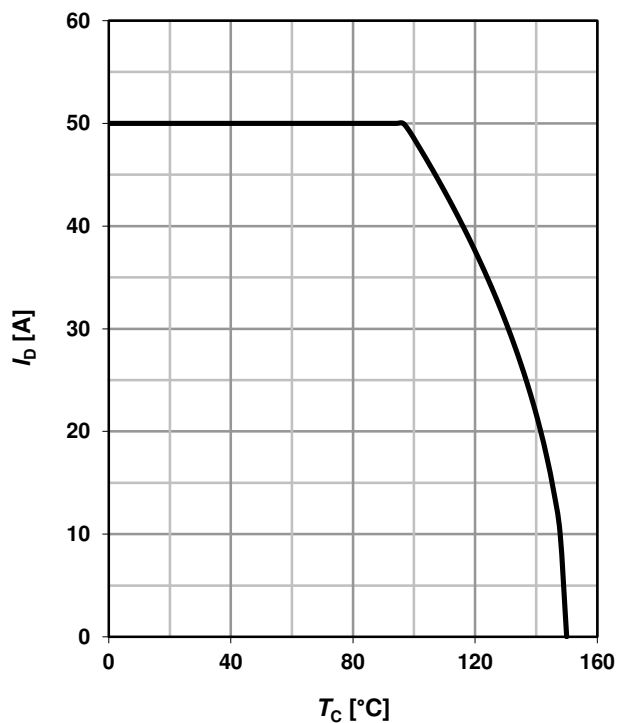
$$P_{\text{tot}} = f(T_A)^{(4)}$$



3 Drain current (Q1)

$$I_D = f(T_C)$$

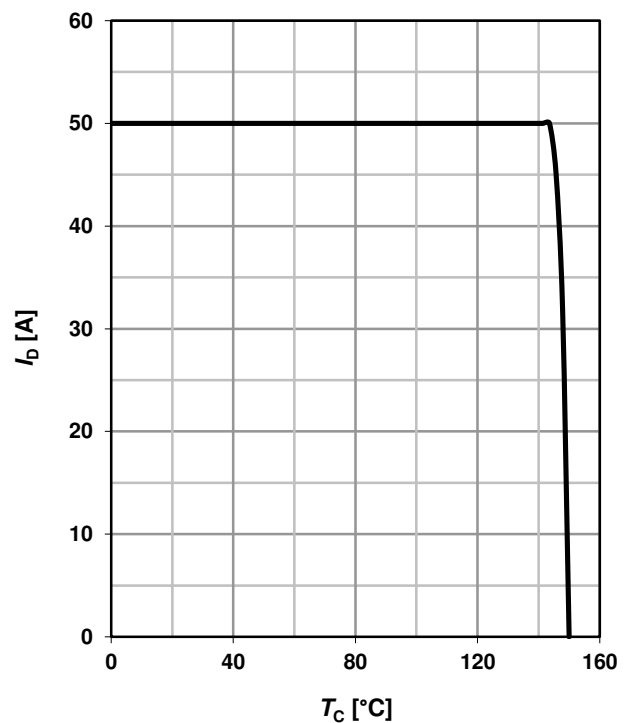
parameter: $V_{GS} \geq 10$ V



4 Drain current (Q2)

$$I_D = f(T_C)$$

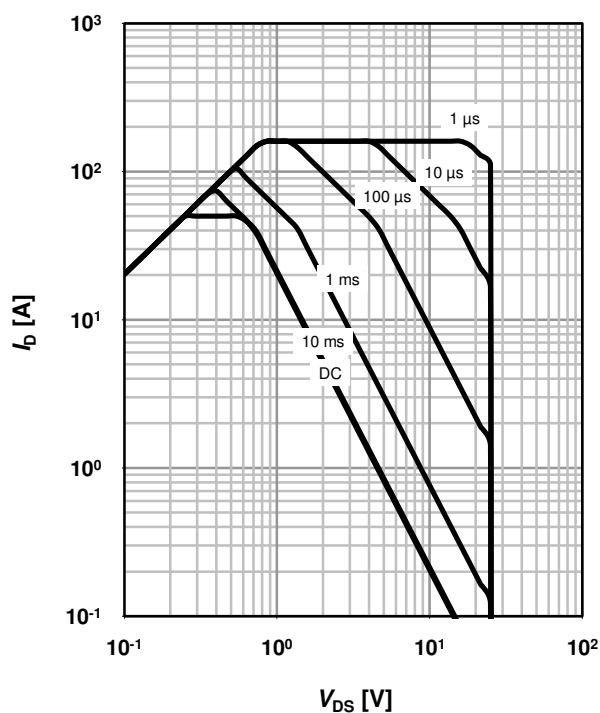
parameter: $V_{GS} \geq 10$ V



5 Safe operating area (Q1)

$$I_D = f(V_{DS}); T_C = 25^\circ\text{C}; D = 0$$

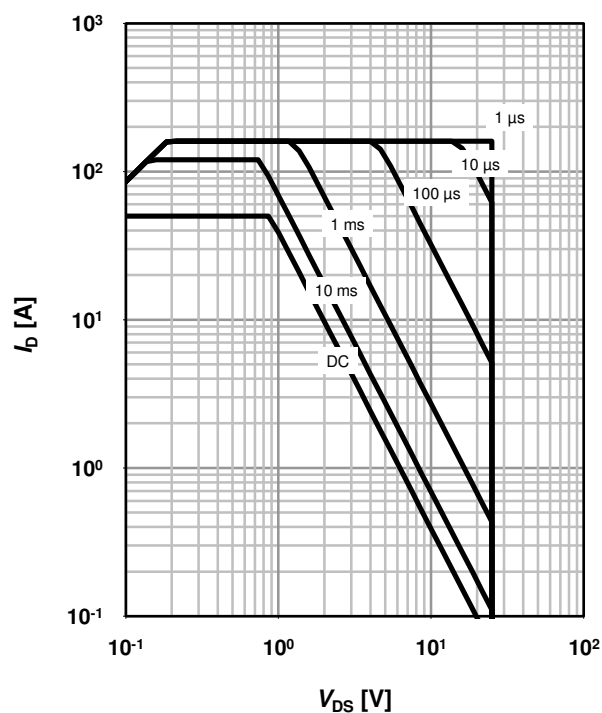
parameter: t_p



6 Safe operating area (Q2)

$$I_D = f(V_{DS}); T_C = 25^\circ\text{C}; D = 0$$

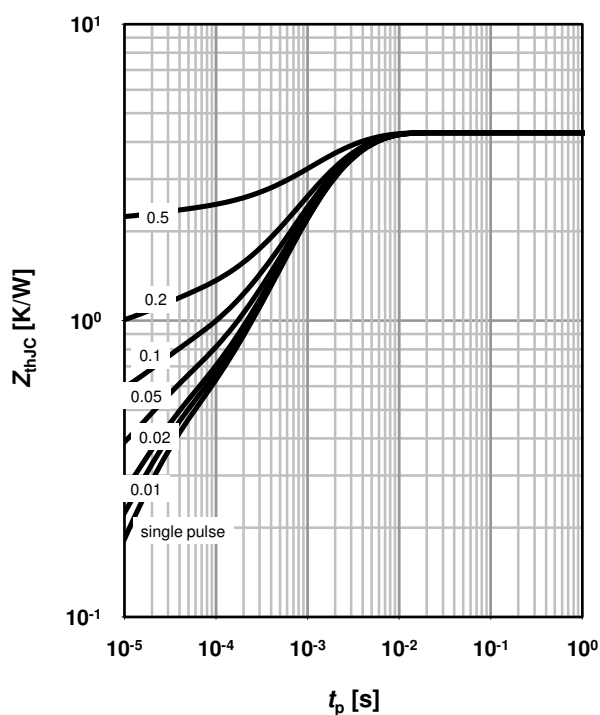
parameter: t_p



7 Max. transient thermal impedance (Q1)

$$Z_{thJC} = f(t_p)$$

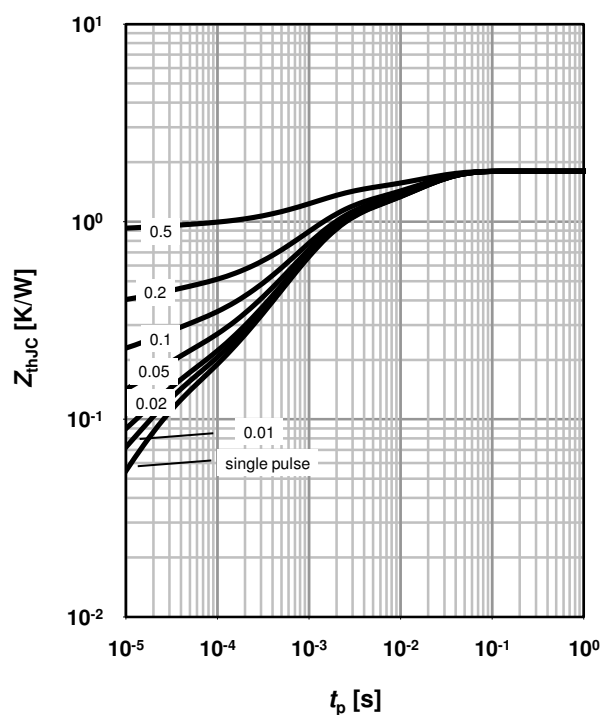
parameter: $D = t_p/T$



8 Max. transient thermal impedance (Q2)

$$Z_{thJC} = f(t_p)$$

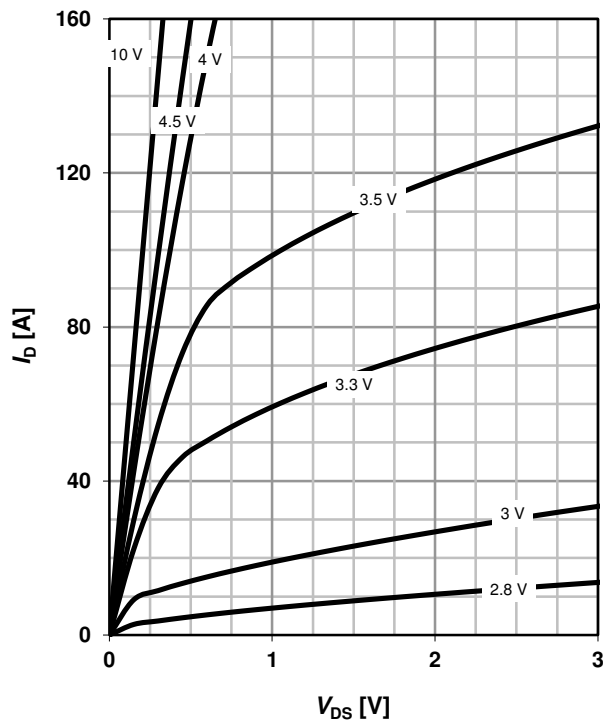
parameter: $D = t_p/T$



9 Typ. output characteristics (Q1)

$$I_D = f(V_{DS}); T_j = 25^\circ\text{C}$$

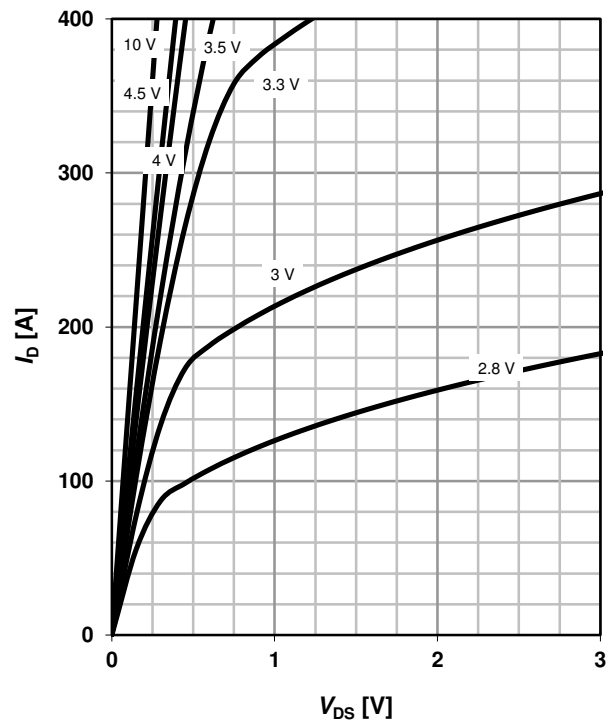
parameter: V_{GS}



10 Typ. output characteristics (Q2)

$$I_D = f(V_{DS}); T_j = 25^\circ\text{C}$$

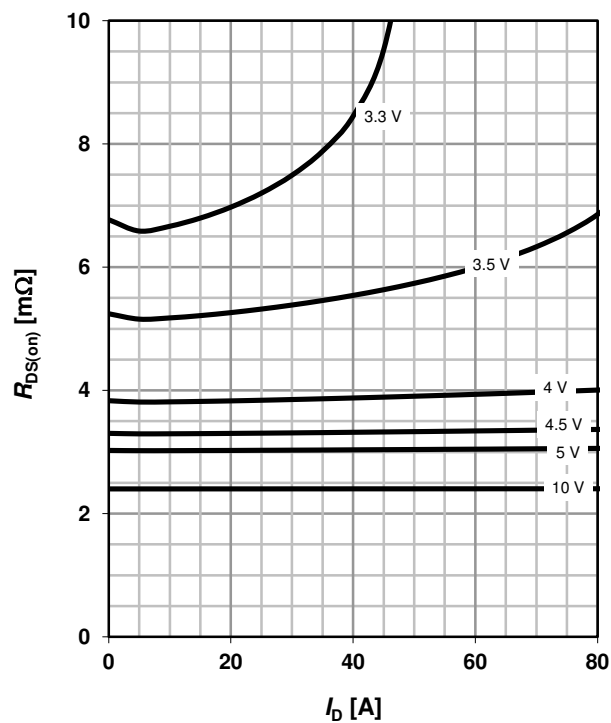
parameter: V_{GS}



11 Typ. drain-source on resistance (Q1)

$$R_{DS(on)} = f(I_D); T_j = 25^\circ\text{C}$$

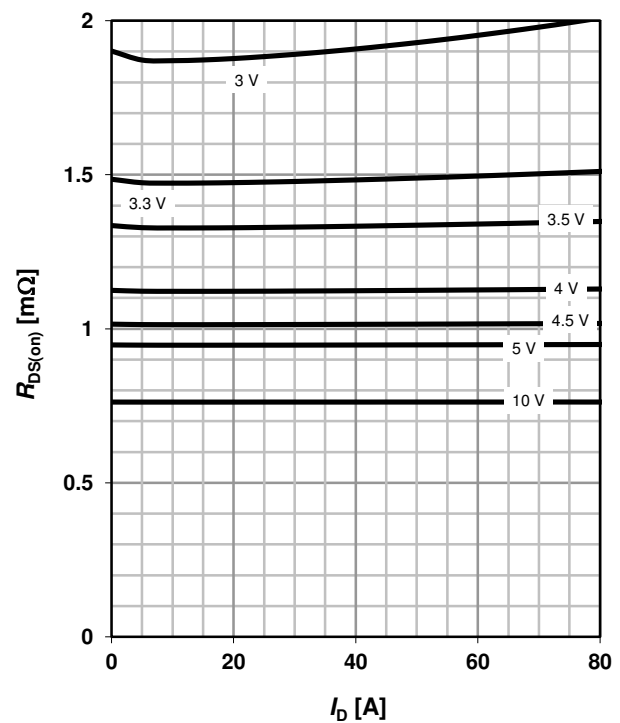
parameter: V_{GS}



12 Typ. drain-source on resistance (Q2)

$$R_{DS(on)} = f(I_D); T_j = 25^\circ\text{C}$$

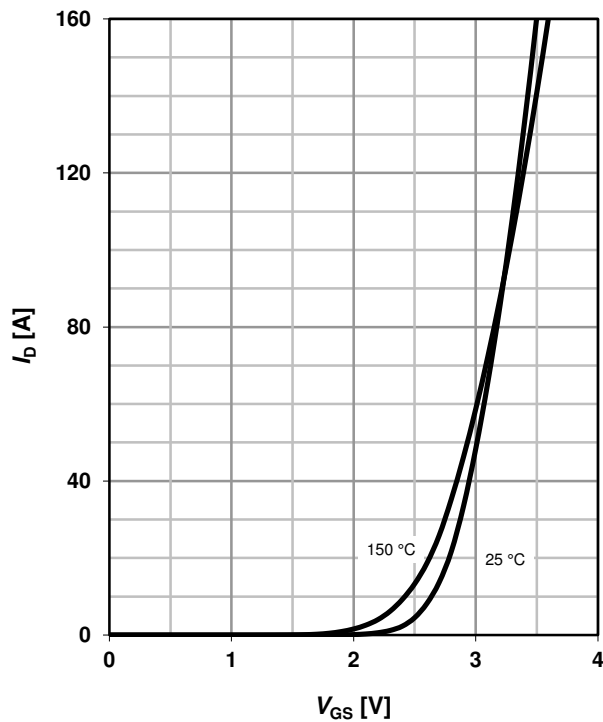
parameter: V_{GS}



13 Typ. transfer characteristics (Q1)

$$I_D = f(V_{GS}); |V_{DS}| > 2 |I_D| R_{DS(on)max}$$

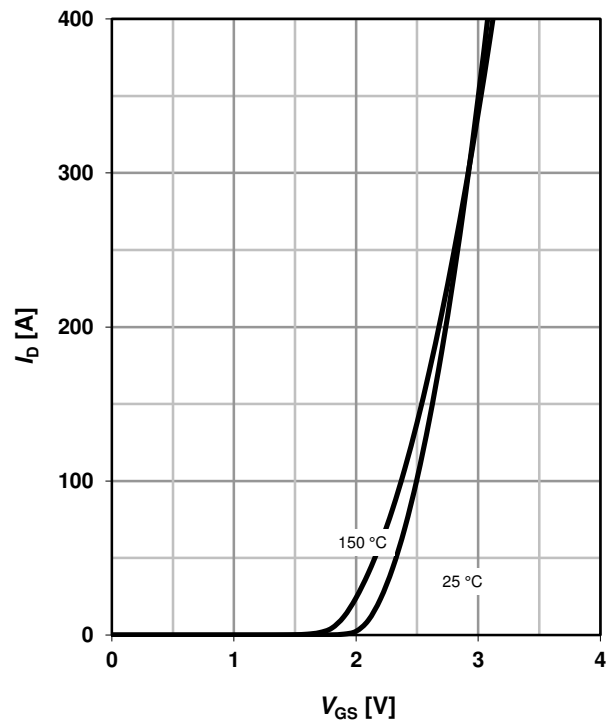
parameter: T_j



14 Typ. transfer characteristics (Q2)

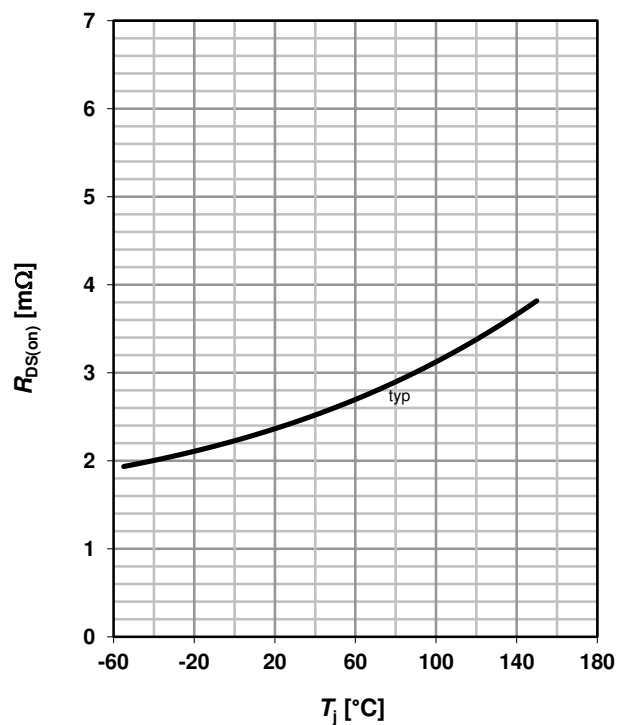
$$I_D = f(V_{GS}); |V_{DS}| > 2 |I_D| R_{DS(on)max}$$

parameter: T_j



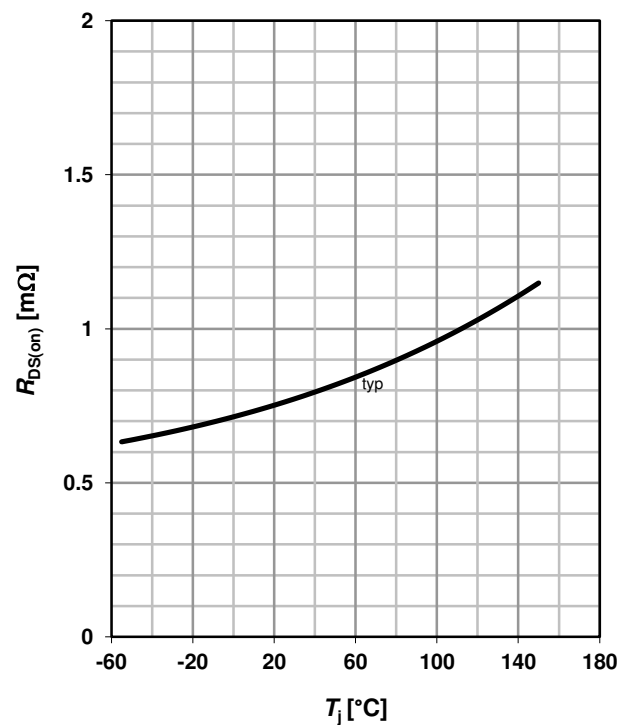
15 Drain-source on-state resistance (Q1)

$$R_{DS(on)} = f(T_j); I_D = 20 \text{ A}; V_{GS} = 10 \text{ V}$$

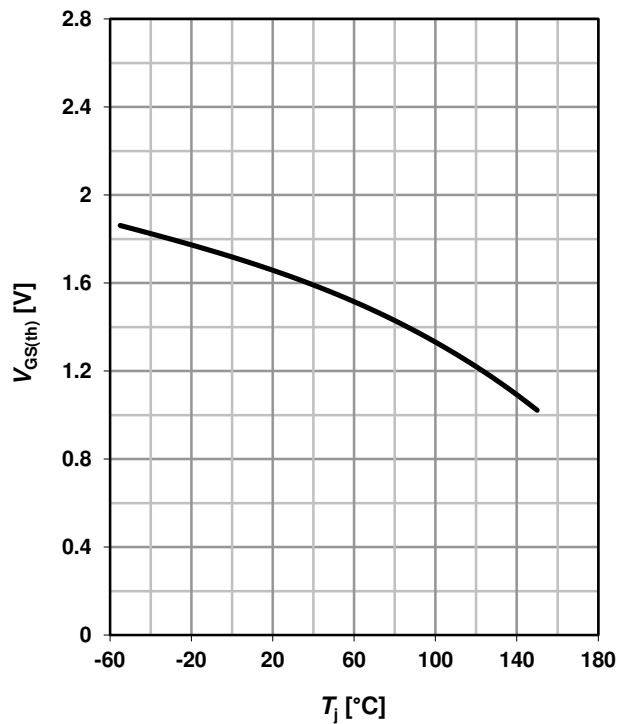


16 Drain-source on-state resistance (Q2)

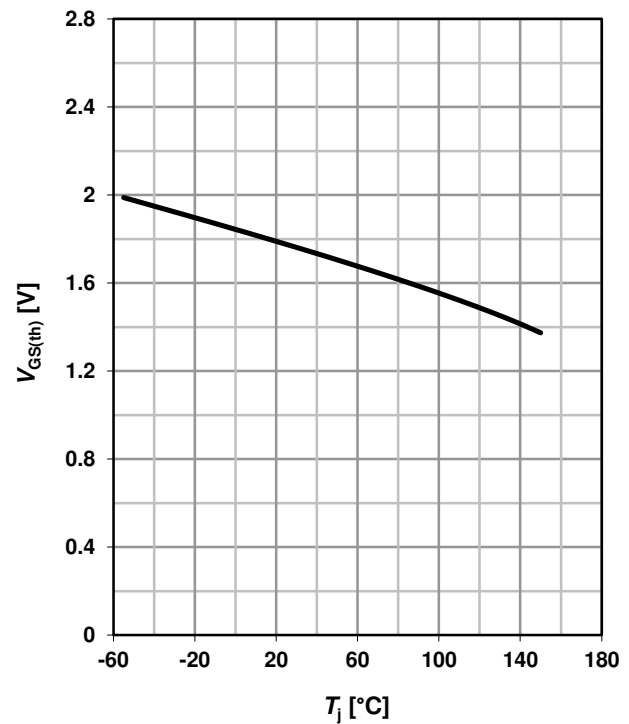
$$R_{DS(on)} = f(T_j); I_D = 20 \text{ A}; V_{GS} = 10 \text{ V}$$



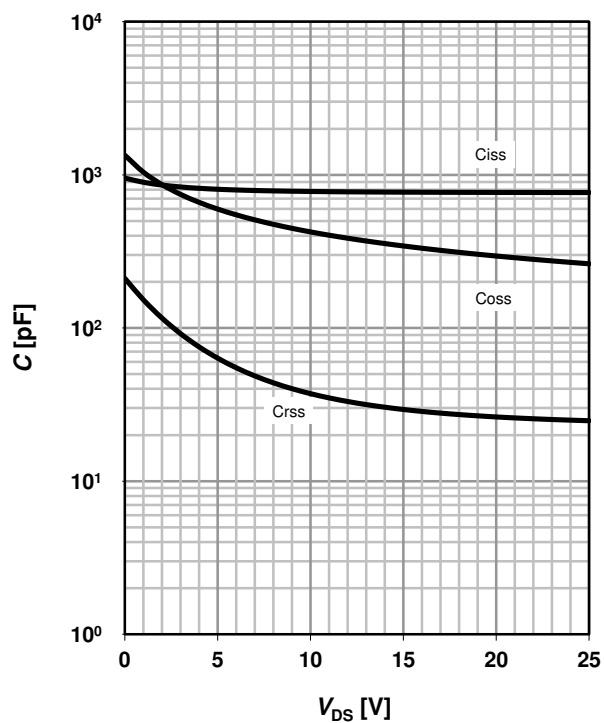
17 Typ. gate threshold voltage (Q1)

 $V_{GS(th)} = f(T_j); V_{GS} = V_{DS}; I_D = 250 \mu A$


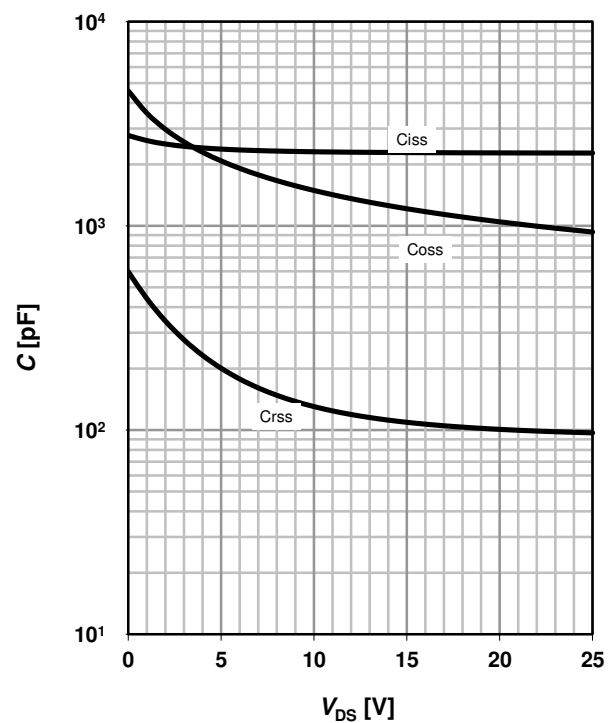
18 Typ. gate threshold voltage (Q2)

 $V_{GS(th)} = f(T_j); V_{GS} = V_{DS}; I_D = 10 \text{ mA}$


19 Typ. capacitances (Q1)

 $C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$


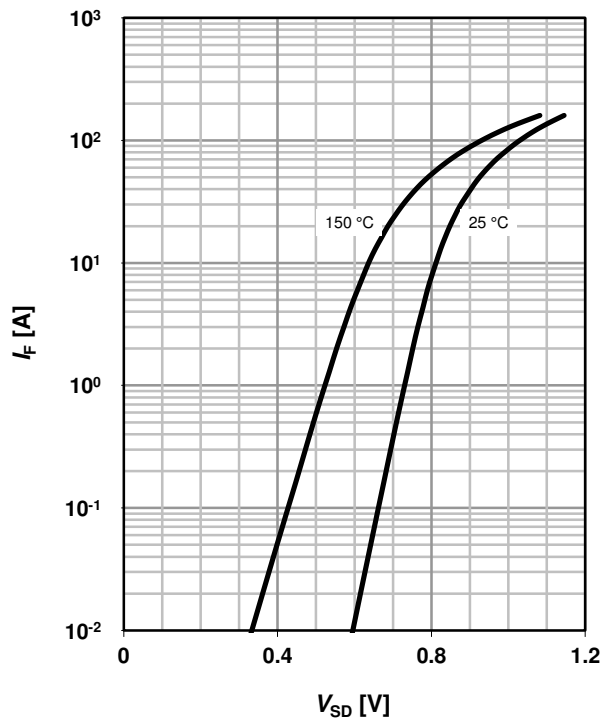
20 Typ. capacitances (Q2)

 $C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$


21 Forward characteristics of reverse diode (Q1)

$$I_F = f(V_{SD})$$

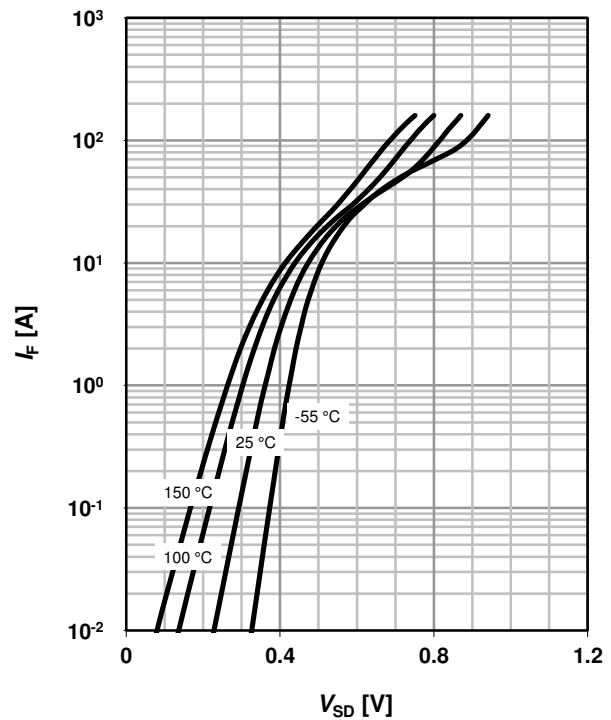
parameter: T_j



22 Forward characteristics of reverse diode (Q2)

$$I_F = f(V_{SD})$$

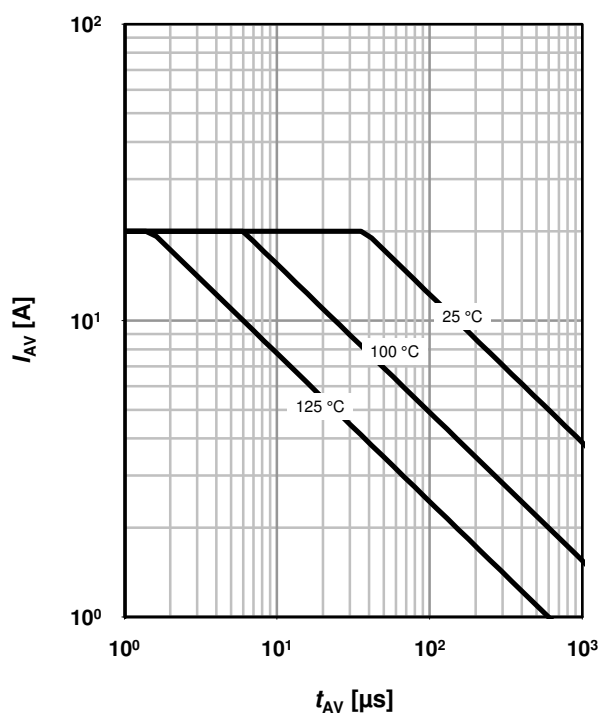
parameter: T_j



23 Avalanche characteristics (Q1)

$$I_{AS} = f(t_{AV}); R_{GS} = 25 \Omega$$

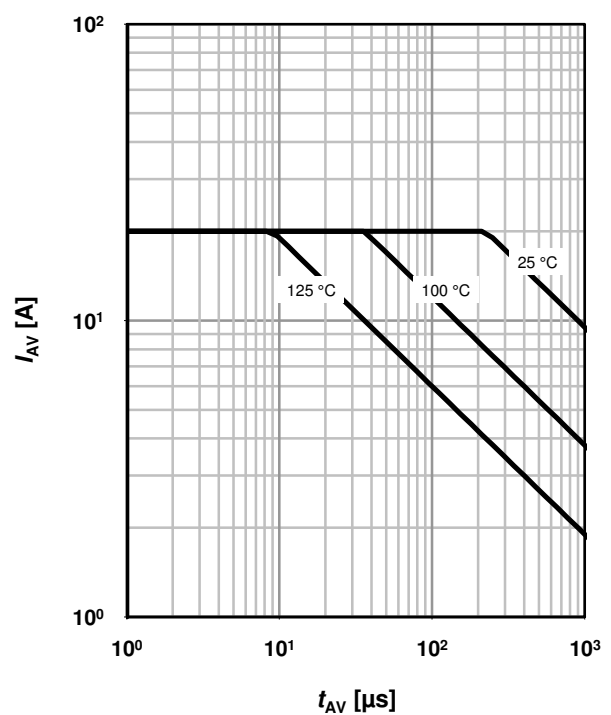
parameter: $T_{j(start)}$



24 Avalanche characteristics (Q2)

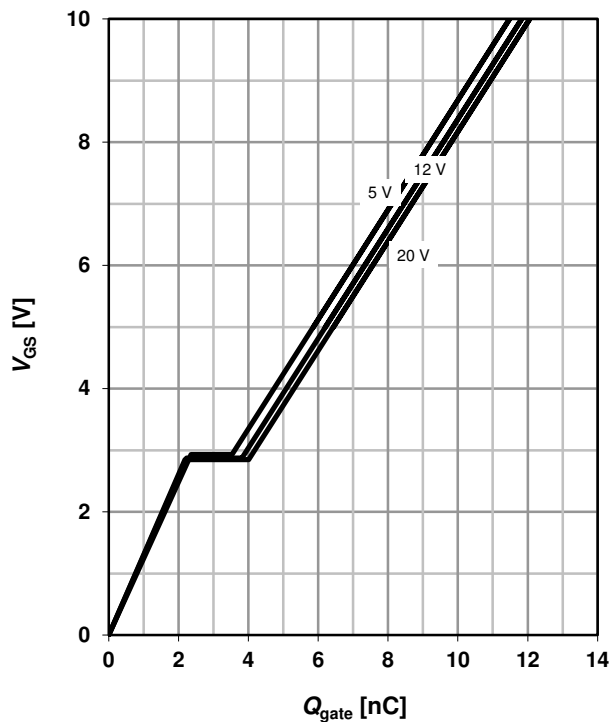
$$I_{AS} = f(t_{AV}); R_{GS} = 25 \Omega$$

parameter: $T_{j(start)}$



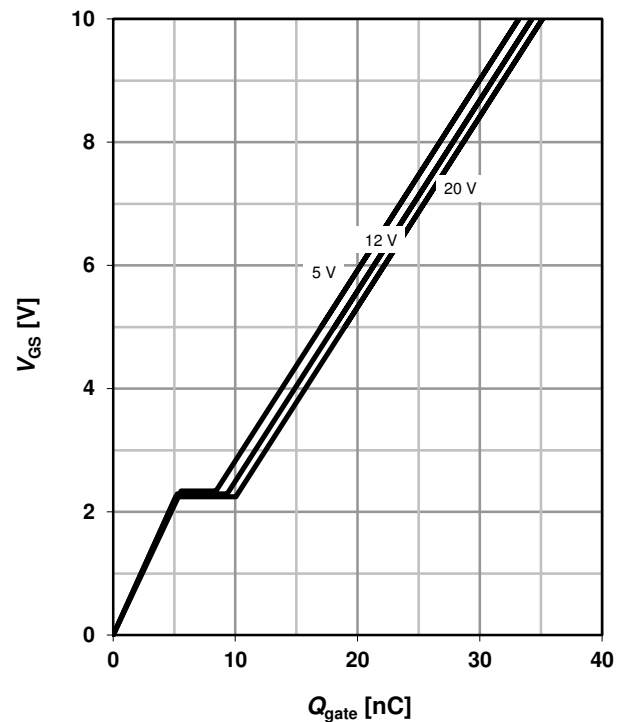
25 Typ. gate charge (Q1)

 $V_{GS}=f(Q_{gate}); I_D=20\text{ A pulsed}$

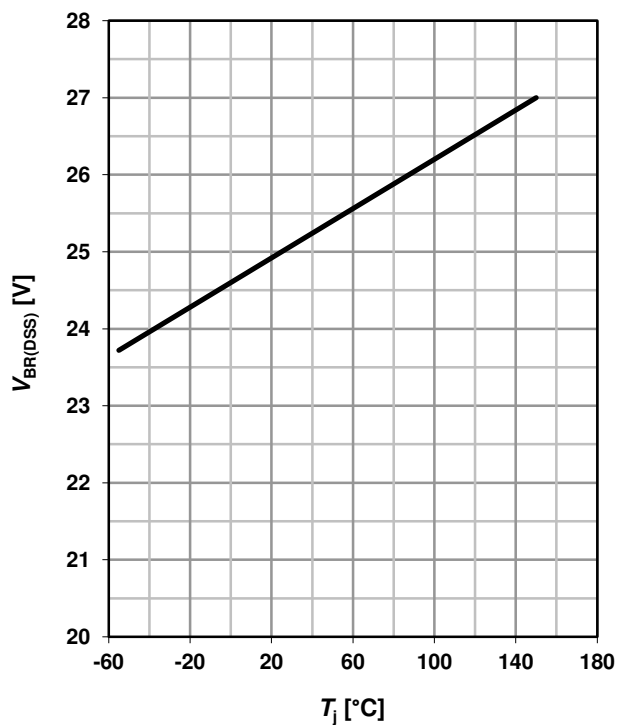
parameter: V_{DD}


26 Typ. gate charge (Q2)

 $V_{GS}=f(Q_{gate}); I_D=20\text{ A pulsed}$

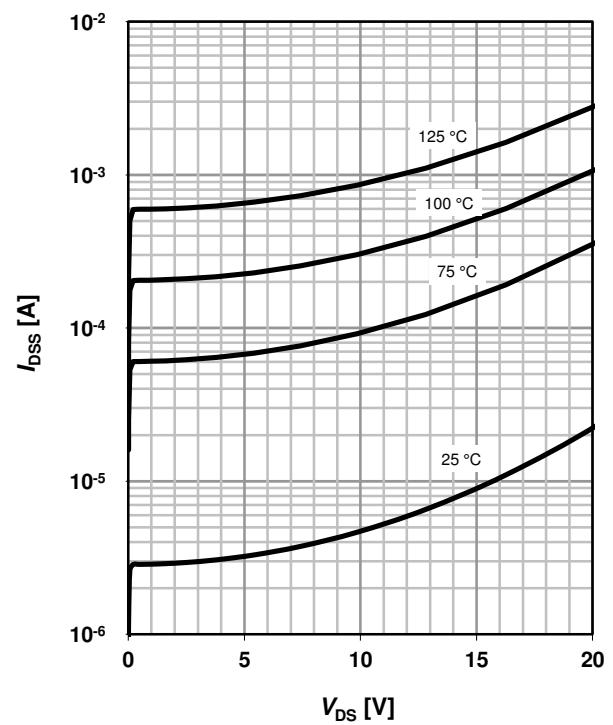
parameter: V_{DD}


27 Drain-source breakdown voltage (Q1)

 $V_{BR(DSS)}=f(T_j); I_D=1\text{ mA}$


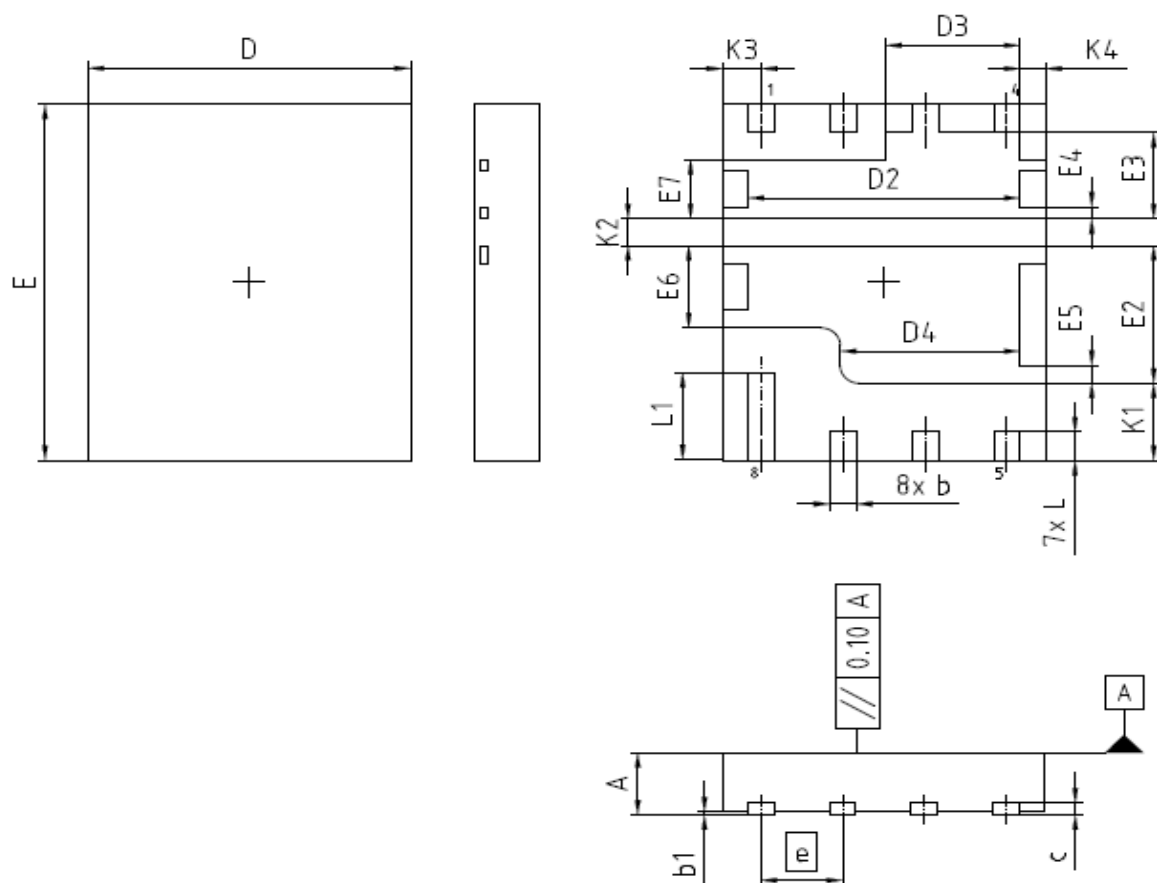
28 Typ. drain-source leakage current (Q2)

 $I_{DSS}=f(V_{DS}); V_{GS}=0\text{ V}$

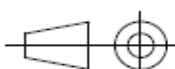
parameter: T_j


Package Outline

PG-TISON8-4

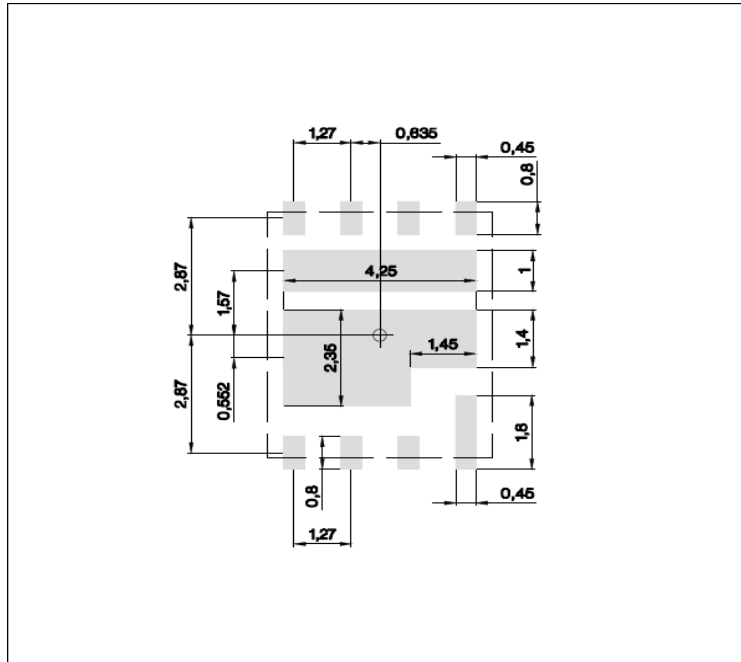


DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.90	1.15	0.035	0.045
b	0.31	0.51	0.012	0.020
b1	0.00	0.05	0.000	0.002
c	0.10	0.30	0.004	0.012
D	4.90	5.10	0.193	0.201
D2	4.12	4.32	0.162	0.170
D3	1.99	2.19	0.078	0.086
D4	2.69	2.89	0.106	0.114
E	5.90	6.10	0.232	0.240
E2	2.22	2.42	0.087	0.095
E3	1.35	1.55	0.053	0.061
E4	0.10	0.30	0.004	0.012
E5	0.20	0.40	0.008	0.016
E6	1.29	1.49	0.051	0.059
E7	0.90	1.10	0.035	0.043
e	1.27 (BSC)		0.05 (BSC)	
N	8		8	
L	0.38	0.58	0.015	0.023
L1	1.38	1.58	0.054	0.062
K1	1.20	1.40	0.047	0.055
K2	0.35	0.55	0.014	0.022
K3	0.50	0.70	0.020	0.028
K4	0.29	0.49	0.011	0.019

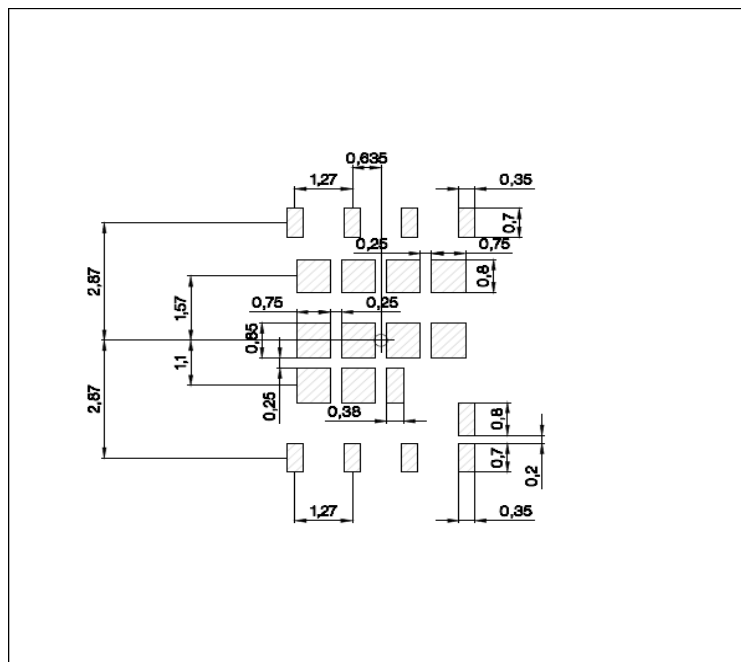
DOCUMENT NO. Z8 B00176527
SCALE 0 2.5 5mm
EUROPEAN PROJECTION 
ISSUE DATE 13-03-2015
REVISION 01

Boardpads & Apertures

PG-TISON8-4



■ copper



▨ stencil apertures

All the dimensions in mm

Revision History

BSG0810NDI

Revision: 2016-03-24, Rev. 2.1

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.0	2015-11-11	Release of final version
2.1	2016-03-24	Update package drawing

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